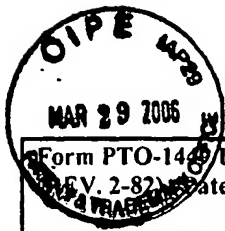


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Form PTO-1449 U.S. Department of Commerce
Patent and Trademark Office**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

(Use several sheets if necessary)

Atty. Docket No.
A35760-PCT-USA
(070050.2713)Serial No.
10/525,288Applicant
James S. ImFiling Date
02/16/2005Group
2813Examiner
*Rodgers***U.S. PATENT DOCUMENTS**

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
<i>CR</i>	1.	3632205	01/04/1972	Marcy
<i>CR</i>	2.	4234358	11/18/1980	Celler et al.
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<i>CR</i>	5.	4456371	06/1984	Lin
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<i>CR</i>	7.	4691983	09/08/1987	Kobayashi et al.
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Examiner

Collier & O'Neil

Date Considered

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<i>CR</i>	16.	4977104	12/11/1990	Sawada et al.
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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
<i>CR</i>	64.	6320227	11/2001	Lee et al.
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<i>CR</i>	75.	6511718	01/18/2003	Paz de Araujo et al.
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	79.	6573531	06/2003	Im et al. duplicated from IDS filed 16 Feb. 2005

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Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
<i>CR</i>	80.	6621044	09/01/2003	Jain et al.
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<i>CR</i>	82.	6526585	03/04/2003	Hill
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<i>CR</i>	85.	20040053450	03/18/2004	Sposili et al.
<i>CR</i>	86.	20020104750	08/08/2002	Ito
<i>CR</i>	87.	RE33836	03/03/1992	Resor, III et al.
	88.	60/253256	08/31/2003	Im
<i>CR</i>	89.	2003096489	05/22/2003	Im et al.
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<i>CR</i>	93.	2004061843	04/01/2004	Im
<i>CR</i>	94.	2005034653	02/17/2005	Im et al.
<i>CR</i>	95.	6563077	05/13/2003	Im

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	Examiner <i>Rodgers</i>	

Exam. Initial.	No.	Document No.	Issue/Publication Date	Applicant(s)
<i>CR</i>	96.	6582827	06/24/2003	Im
<i>CR</i>	97.	6830993	12/14/2004	Im et al.

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Examiner

*Colleen E. Goff*Date Considered *23 March 2007*

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	Filing Date 02/16/2005	Group 2813
	Examiner <i>Rodgers</i>	

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Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
<i>CR</i>	98.	681316	08/11/1995	EP		
<i>CR</i>	99.	1067593	10/01/2001	EP		
<i>CR</i>	100.	655774	07/17/1996	EP		
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<i>CR</i>	105.	6252048	09/09/1994	JP		<u>No</u>
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<i>CR</i>	108.	11064883	03/05/1999	JP		<u>No</u>
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<i>CR</i>	110.	2001023920	01/26/2001	JP		
<i>CR</i>	111.	62181419	08/08/1987	JP		
<i>CR</i>	112.	9824118	06/04/1998	WO		

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	Examiner <i>Rodgers</i>	

Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
<i>CR</i>	113.	9931719	06/24/1999	WO		<u>No</u>
<i>CR</i>	114.	0014784	03/16/2000	WO		
<i>CR</i>	115.	0118854	03/15/2001	WO		
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<i>CR</i>	124.	03018882	03/06/2003	WO		
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Exam Initial	No.	Document No.	Publication Date	Country	Translation	
					Yes	No
<i>ce</i>	129.	04017380	02/26/2004	WO		
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Collette E. Ruf

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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
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<i>CR</i>	148.	S.D. Brotherton, "Polycrystalline Silicon Thin Film Transistors," 10 Semicond. Sci. Tech., pp. 721-738 (1995).
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NY02:543906.1	Examiner <i>Colleen E. Prof</i>	Date Considered <i>23 March 2007</i>
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Exam Initial	No.	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, Etc.)
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Examiner

Colleen J. Rodgers

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23 March 2007

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